Product data sheet

# 1. General description

AC Thyristor Triac power switch in a SOT428 (DPAK) surface mountable plastic package with self-protective clamping capabilities against low and high energy transients.

#### 2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- · Direct interfacing with low power drivers and microcontrollers
- · Full cycle AC conduction
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- · Protective self turn-on capability for high energy transients
- Safe clamping capability for low energy over-voltage transients
- · Sensitive gate for easy logic level triggering
- Surface mountable package
- · Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt

# 3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- · Large and small appliances (White Goods)
- Reversing induction motor controls

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off- state voltage		-	-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 115 ^{\circ}\text{C}$ ; Fig. 1; Fig. 2; Fig. 3	-	-	2	Α
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$	-	-	15.4	Α
		full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	-	14	Α
Tj	junction temperature		-	-	125	°C
V <sub>PP</sub>	peak pulse voltage	T <sub>j</sub> = 25 °C; non-repetitive, off-state; Fig. 6	-	-	2	kV

## **AC Thyristor Triac power switch**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G+;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 8}}{\text{C}}$	_	-	10	mA
		$V_D$ = 12 V; $I_T$ = 100 mA; LD+ G-; $T_j$ = 25 °C; Fig. 8	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD- G-;}$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	10	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	-	25	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 3 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	-	2	V
$V_{CL}$	clamping voltage	$I_{CL} = 0.1 \text{ mA}; t_p = 1 \text{ ms}; T_j = 25 \text{ °C}$	850	-	-	V
Dynamic ch	aracteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 125 °C; $(V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit; Fig. 13	500	-	-	V/µs
dI <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 2 A; $dV_{com}/dt$ = 10 V/ $\mu$ s; gate open circuit; Fig. 14; Fig. 15	3	-	-	A/ms

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	CM	common		LD -
2	LD	load	(7 B S)	
3	G	gate		G—/
mb	LD	mounting base; load	DPAK (SOT428)	CM 003aaf296

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package					
	Name	Description	Version			
ACTT2S-800E	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428			

**AC Thyristor Triac power switch** 

# 7. Limiting values

#### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 115 °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	2	Α
I <sub>TSM</sub>	non-repetitive peak on-	full sine wave; $T_{j(init)} = 25  ^{\circ}C$ ; $t_p = 16.7  ms$	-	15.4	Α
	state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	14	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; sine-wave pulse	-	0.98	A²s
dl <sub>T</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 20 mA	-	100	A/µs
I <sub>GM</sub>	peak gate current	t = 20 μs	-	2	Α
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
Tj	junction temperature		-	125	°C
$V_{PP}$	peak pulse voltage	T <sub>j</sub> = 25 °C; non-repetitive, off-state; <u>Fig. 6</u>	-	2	kV

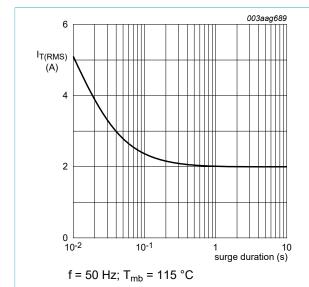


Fig. 1. RMS on-state current as a function of surge duration; maximum values

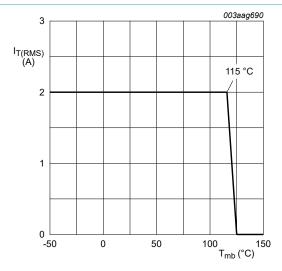


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

## **AC Thyristor Triac power switch**

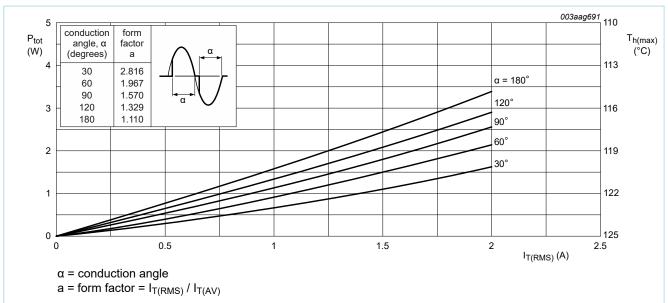


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

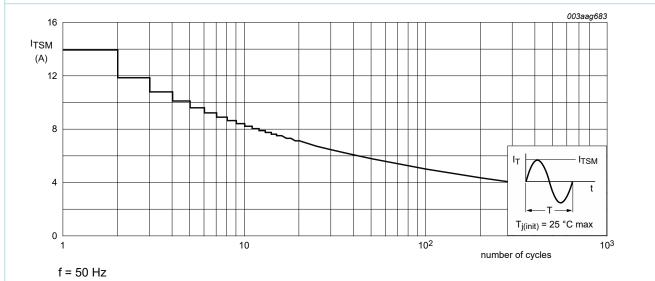


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

#### **AC Thyristor Triac power switch**

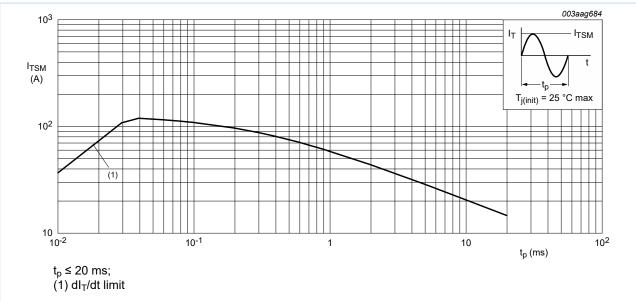


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

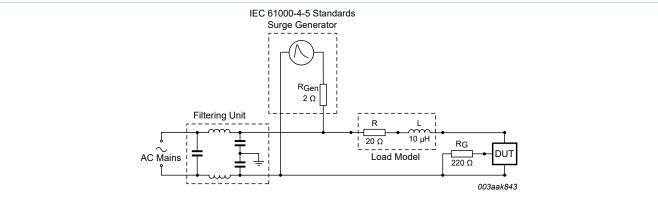


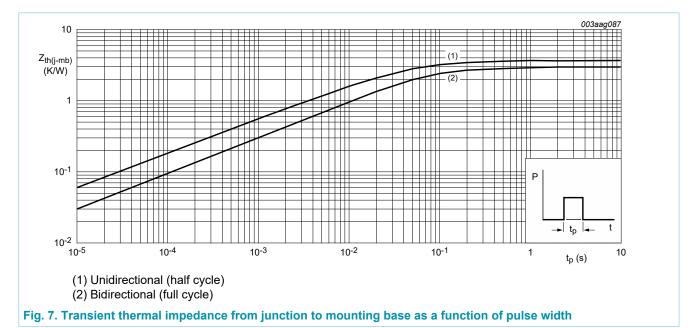
Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

**AC Thyristor Triac power switch** 

## 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	full cycle; Fig. 7	-	-	3	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted	-	75	-	K/W



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**AC Thyristor Triac power switch** 

## 9. Characteristics

#### **Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		,			
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 100 \text{ mA}; LD+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G-;}$ $T_j = 25 \text{ °C; Fig. 8}$	-	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; LD- G-; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	10	mA
l <sub>L</sub>	latching current	$V_D = 12 \text{ V}; I_G = 100 \text{ mA}; LD+ G+;$ $T_j = 25 \text{ °C}; Fig. 9$	-	-	25	mA
		$V_D = 12 \text{ V}; I_G = 100 \text{ mA}; LD+ G-;$ $T_j = 25 \text{ °C}; Fig. 9$	-	-	30	mA
		$V_D = 12 \text{ V}; I_G = 100 \text{ mA}; LD- G-;$ $T_j = 25 \text{ °C}; Fig. 9$	-	-	25	mA
lн	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	-	25	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 3 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	-	2	V
$V_{GT}$	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; T <sub>j</sub> = 25 °C; Fig. 12	-	0.8	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 100 mA; T <sub>j</sub> = 125 °C; Fig. 12	0.2	0.45	-	V
l <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
		V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	-	0.5	mA
V <sub>CL</sub>	clamping voltage	$I_{CL}$ = 0.1 mA; $t_p$ = 1 ms; $T_j$ = 25 °C	850	-	-	V
Dynamic cl	naracteristics			'	'	
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 125 °C; $(V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit; Fig. 13	500	-	-	V/µs
dl <sub>com</sub> /dt	rate of change of commutating current	$V_D = 400 \text{ V}$ ; $T_j = 125 \text{ °C}$ ; $I_{T(RMS)} = 2 \text{ A}$ ; $dV_{com}/dt = 10 \text{ V/}\mu\text{s}$ ; gate open circuit; Fig. 14; Fig. 15	3	-	-	A/ms

#### **AC Thyristor Triac power switch**

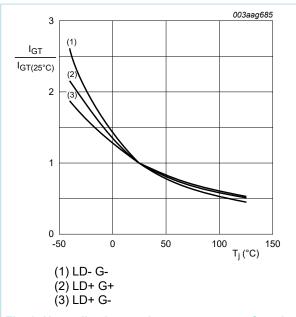


Fig. 8. Normalized gate trigger current as a function of junction temperature

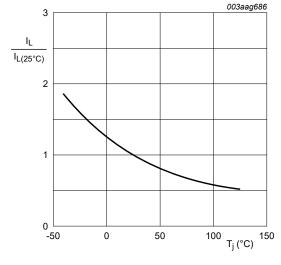


Fig. 9. Normalized latching current as a function of junction temperature

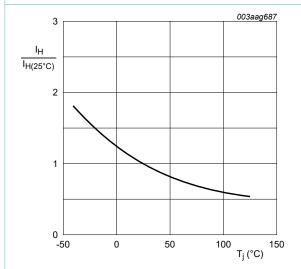
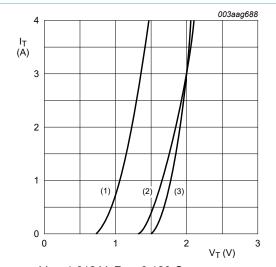


Fig. 10. Normalized holding current as a function of junction temperature



 $V_o$  = 1.612 V;  $R_s$  = 0.120  $\Omega$ 

(1) T<sub>j</sub> = 125 °C; typical values (2) T<sub>j</sub> = 125 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig. 11. On-state current as a function of on-state voltage

#### **AC Thyristor Triac power switch**

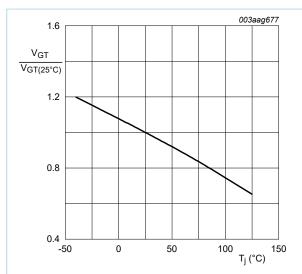
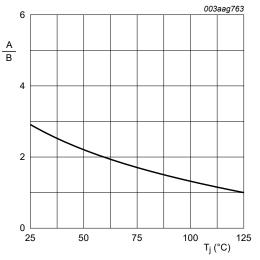
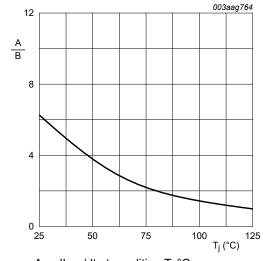


Fig. 12. Normalized gate trigger voltage as a function of junction temperature



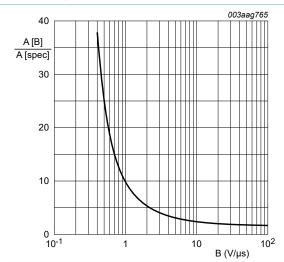
A =  $dV_D/dt$  at condition  $T_j$  °C B =  $dV_D/dt$  at condition  $T_i$  [125] °C

Fig. 13. Normalized rate of rise of off-state voltage as a function of junction temperature



A =  $dI_{com}/dt$  at condition  $T_j$  °C B =  $dI_{com}/dt$  at condition  $T_j$  [125] °C  $V_D$  = 400 V

Fig. 14. Normalized critical rate of rise of commutating current as a function of junction temperature

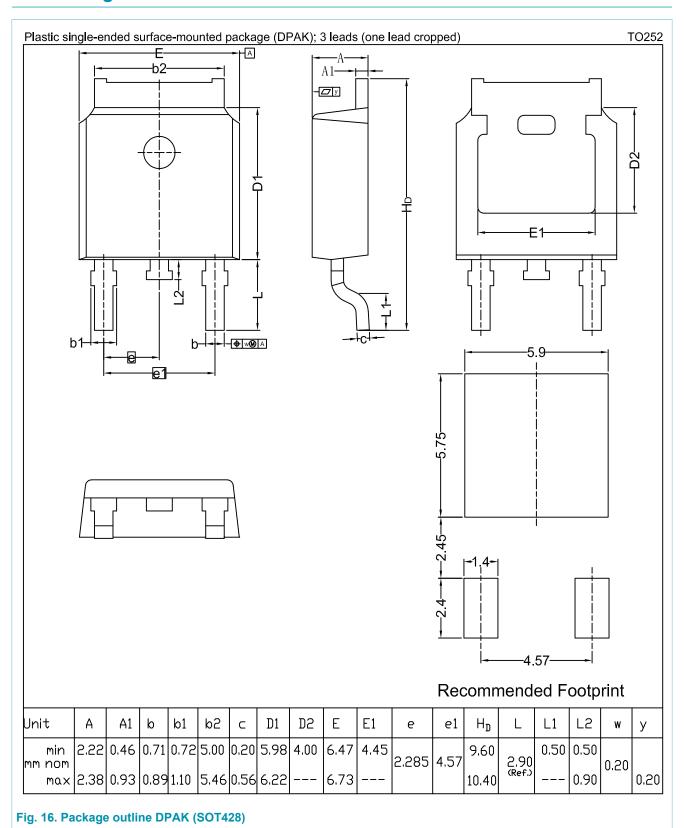


A [B] =  $dI_{com}/dt$  at condition B,  $dV_{com}/dt$ A [spec] is the data sheet value for  $dI_{com}/dt$ turn-off time is less than 20 ms

Fig. 15. Normalized critical rate of change of commutating current as a function of critical rate of change of commutating voltage; minimum values

**AC Thyristor Triac power switch** 

# 10. Package outline



#### **AC Thyristor Triac power switch**

# 11. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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**AC Thyristor Triac power switch** 

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#### **AC Thyristor Triac power switch**

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